

LAMINATE AND MANUFACTURING METHOD OF SEMICONDUCTOR DEVICE

ABSTRACT

Provided is a laminate that can be implemented with a wide processing margin and without adhesive residue or damage to a semiconductor element in the transfer of the semiconductor element using laser light of various wavelengths. The laminate is obtained by laminating a substrate 1 having laser permeability, a resin film 1 and a resin film 2 in this order, wherein the light absorbance of the resin film 1 calculated for a film thickness of 1.0 μm at any wavelength of 200 nm to 1100 nm is 0.4-5.0, and the adhesive strength of the surface of the resin film 2 on the side opposite that of the resin film 1 side is 0.02-0.3 N/cm.

[Fig.1]